

SANYO

No.2461

2SC4071

NPN Epitaxial Planar Type Silicon Transistor
 DIFFERENTIAL AMP,
 VERY HIGH-SPEED SWITCHING APPLICATIONS

Features

The 2SC4071 is formed with two chips, being equivalent to the 2SC3770, placed in one package.

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V_{CB0}	30	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EB0}	3	V
Collector Current	I_C	30	mA
Base Current	I_B	10	mA
Collector Dissipation	P_C	250	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

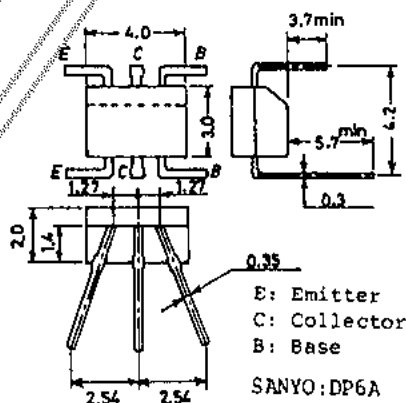
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=20V, I_E=0$			1.0	µA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=2V, I_C=0$			10	µA
DC Current Gain	h_{FE}	$V_{CE}=10V, I_C=3mA$	40		200	
DC Current Gain Ratio	h_{FE1}/h_{FE2}	$V_{CE}=10V, I_C=3mA, *1$	0.8		1.0	
Base to Emitter Voltage Difference	ΔV_{BE}	$V_{CE}=10V, I_C=3mA$			10	mV
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=3mA, *2$	0.6	1.2		GHz
Collector Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz, *2$		0.7		pF

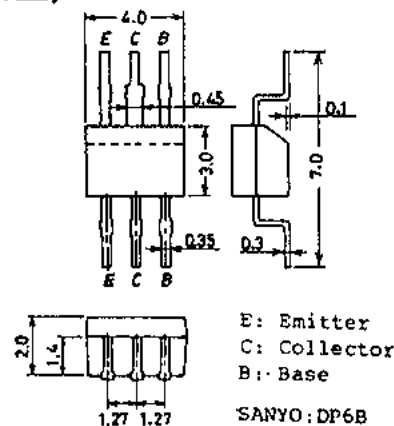
*1: The smaller h_{FE} is taken as h_{FE1} .

*2: Chips in the same lot are evaluated as the 2SC3770.

Case Outline 2029A
 (unit:mm)



Case Outline 2030A
 (unit:mm)



The application circuit diagrams and circuit constants herein are included as an example and providing guarantee for designing equipment to be mass-produced.
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